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NAKAYAMA ET AL.

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May 31, 2006

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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

TRANSLATION

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

↓	Zhang et al, "Transmission Electron Microscopy Investigation of Dislocations in Forward-biased 4H-SiC p-i-n Diodes", Applied Physics Letters AIP USA, vol. 83, no. 16, 20 October 2003, pp. 3320-3322 Saddow et al, "Thermal Capacitance Spectroscopy of Epitaxial 3C and 6H-Sic pn Junction Diodes Grown Side By Side on a 6H-SiC Substrate", Applied Physics Letters, AIP, American Institute of Physics, Melville, NY, vol. 66, no. 26, 26 June 1995

*Examiner /Telly Green/ Date Considered 03/11/2009

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

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